

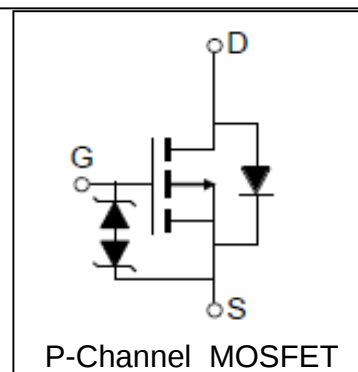
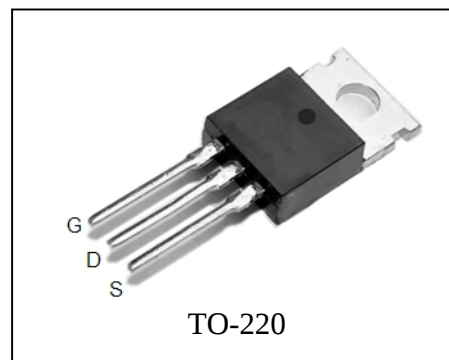
Features

- -60V/-16A,
 $R_{DS(ON)} = 100m\Omega(Typ.) @ V_{GS} = -10V$
 $R_{DS(ON)} = 125m\Omega(Typ.) @ V_{GS} = -4.5V$
- Super High Dense Cell Design
- ESD protected
- Reliable and Rugged
- 100% avalanche tested
- Lead Free and Green Devices Available
 (RoHS Compliant)

Applications

- Power Management
- Load Switch
- DC/DC Converter

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		-60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	-16	A
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	-64 ^①	A
I _D	Continuous Drain Current(V _{GS} =-10V)	T _C =25°C	-16	A
		T _C =100°C	-11	
P _D	Maximum Power Dissipation	T _C =25°C	54	W
		T _C =100°C	27	
R _{θJC}	Thermal Resistance-Junction to Case		2.8	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^②	Avalanche Energy, Single Pulsed		72	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU55L18R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -60V, V _{GS} =0V			-1	μA
		T _J =85°C			-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1		-3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V			±10	μA
R _{DS(ON)} ③	Drain-Source On-state Resistance	V _{GS} = -10V, I _{DS} =-9A		100	115	mΩ
		V _{GS} = -4.5V, I _{DS} =-7A		125	150	mΩ
Diode Characteristics						
V _{SD} ③	Diode Forward Voltage	I _{SD} =-18A, V _{GS} =0V			-1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =-1A, dI _{SD} /dt=100A/μs		16		ns
Q _{rr}	Reverse Recovery Charge			29		nC
Dynamic Characteristics ④						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		12		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = -30V, Frequency=1.0MHz		910		pF
C _{oss}	Output Capacitance			625		
C _{rss}	Reverse Transfer Capacitance			170		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =2Ω, I _{DS} =-16A, V _{GEN} =-10V, R _G =6Ω		15		ns
t _r	Turn-on Rise Time			23		
t _{d(OFF)}	Turn-off Delay Time			33		
t _f	Turn-off Fall Time			18		
Gate Charge Characteristics ④						
Q _g	Total Gate Charge	V _{DS} =-48V, V _{GS} = -10V, I _{DS} =-16A		32		nC
Q _{gs}	Gate-Source Charge			5		
Q _{gd}	Gate-Drain Charge			11		

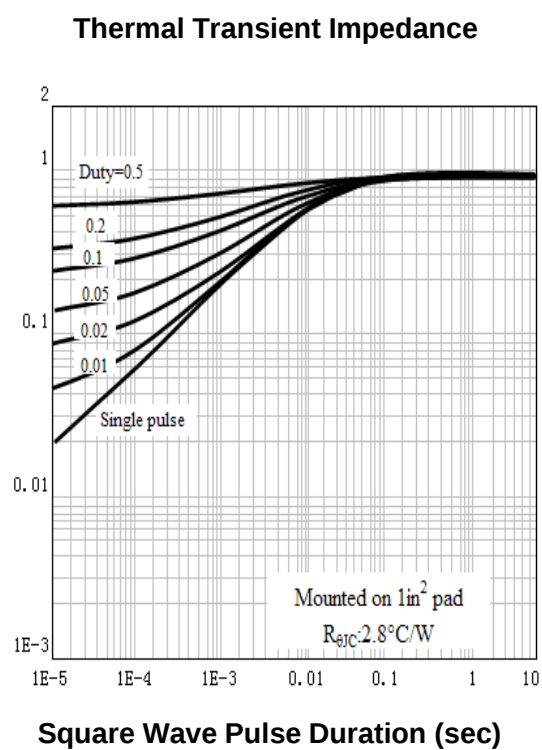
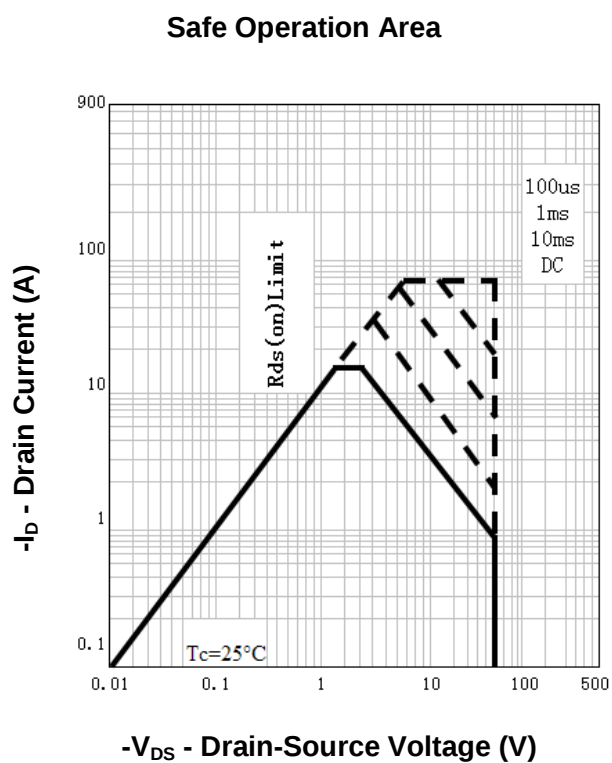
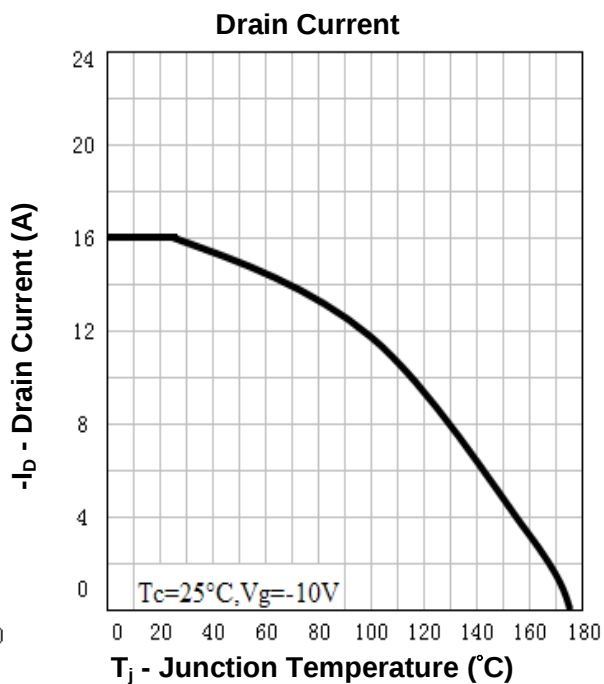
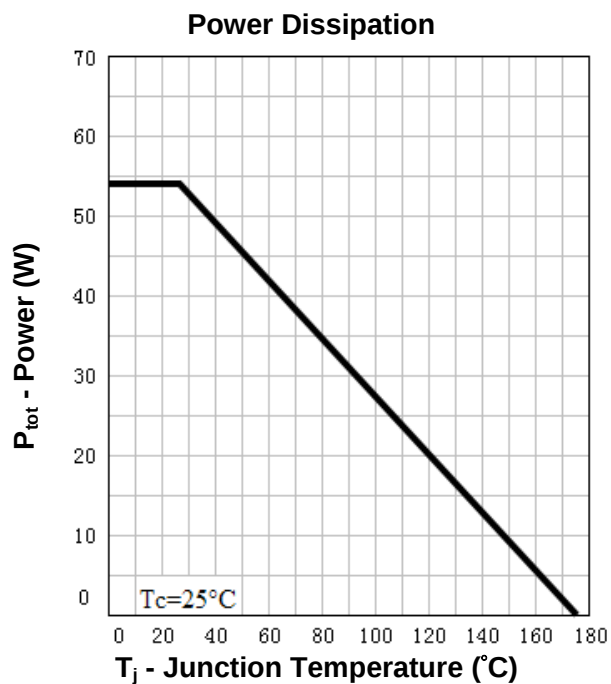
Notes: ① Pulse width limited by safe operating area.

② Limited by T_{Jmax} , $I_{AS}=-17A$, $V_{DD}=-48V$, $R_G=50\Omega$, Starting $T_J=25^{\circ}\text{C}$.

③ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

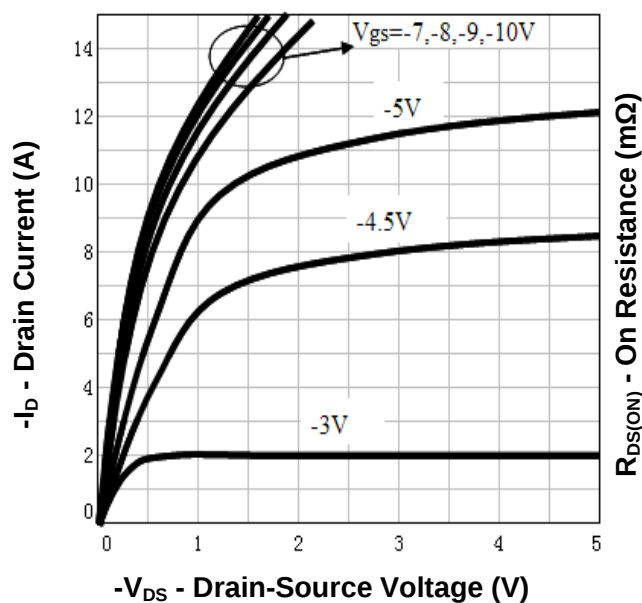
④ Guaranteed by design, not subject to production testing.

Typical Characteristics

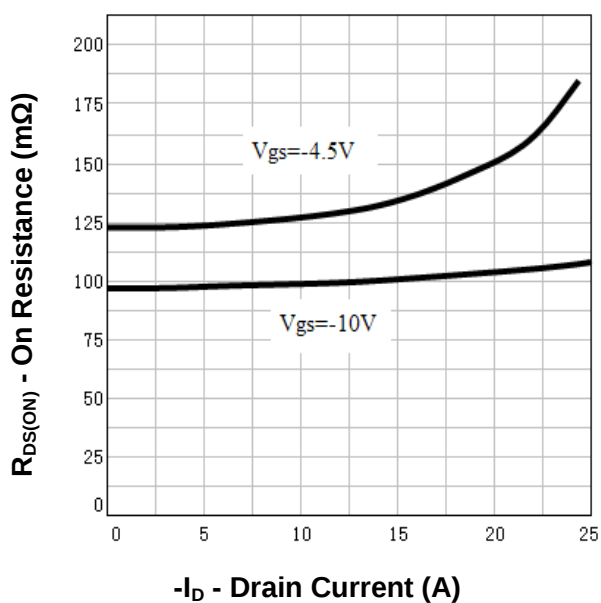


Typical Characteristics

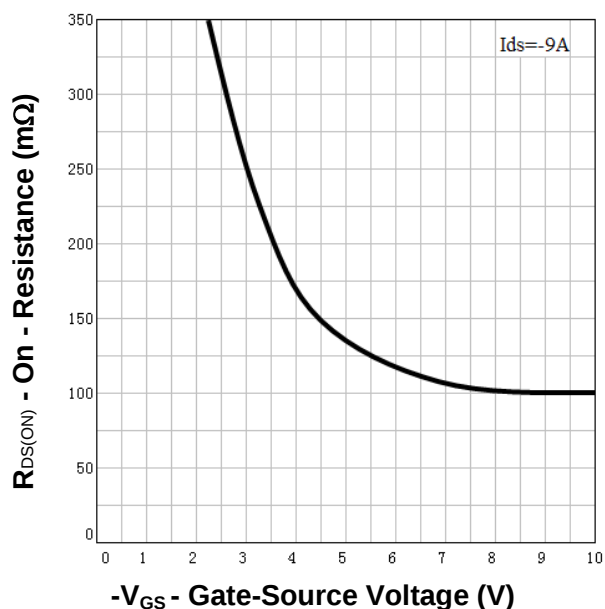
Output Characteristics



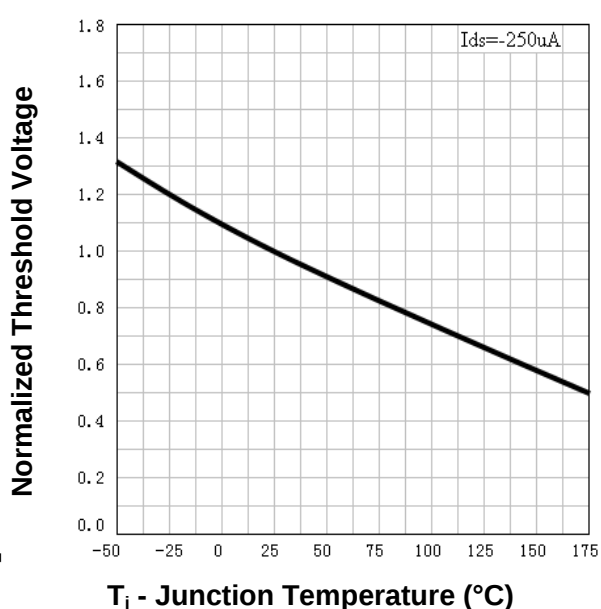
Drain-Source On Resistance



Drain-Source On Resistance

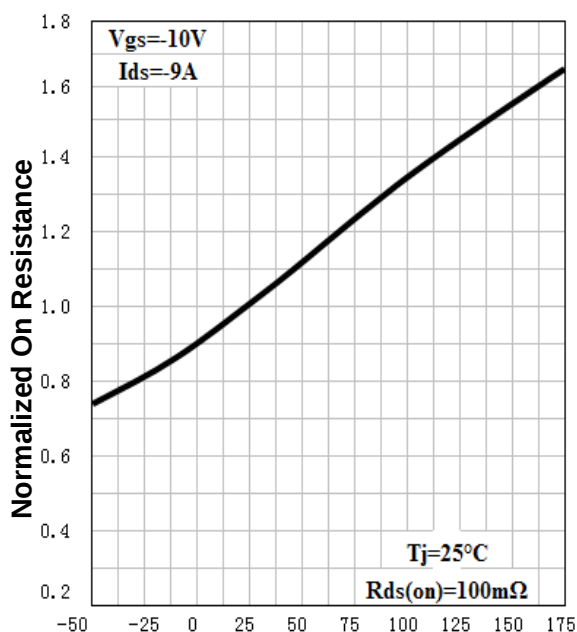


Gate Threshold Voltage



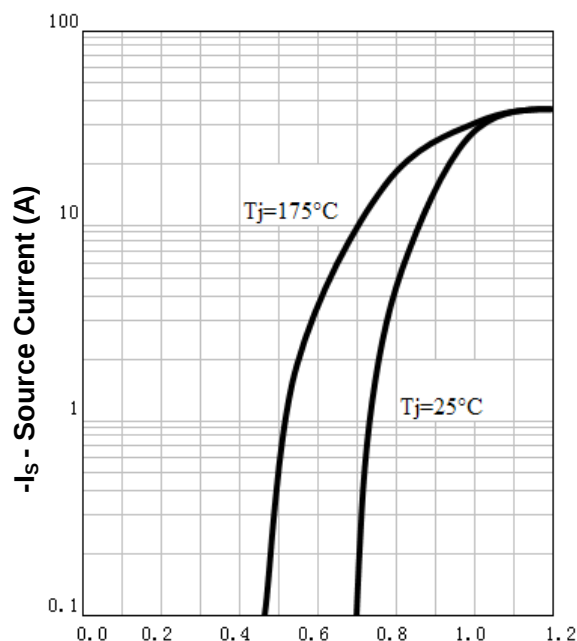
Typical Characteristics

Drain-Source On Resistance



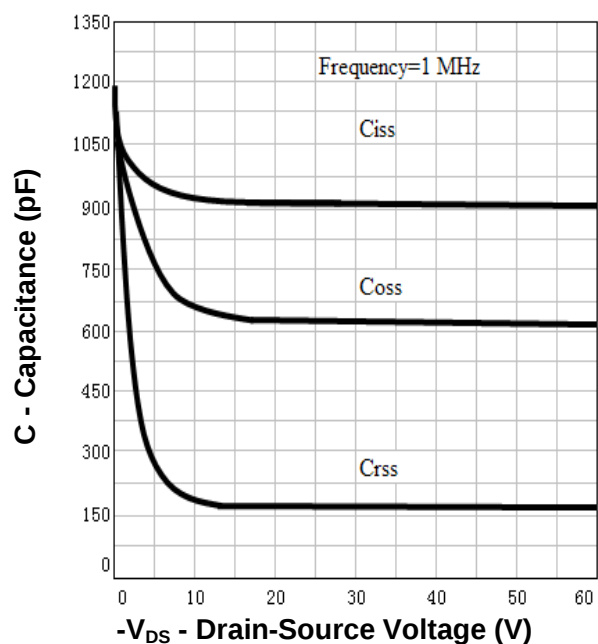
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



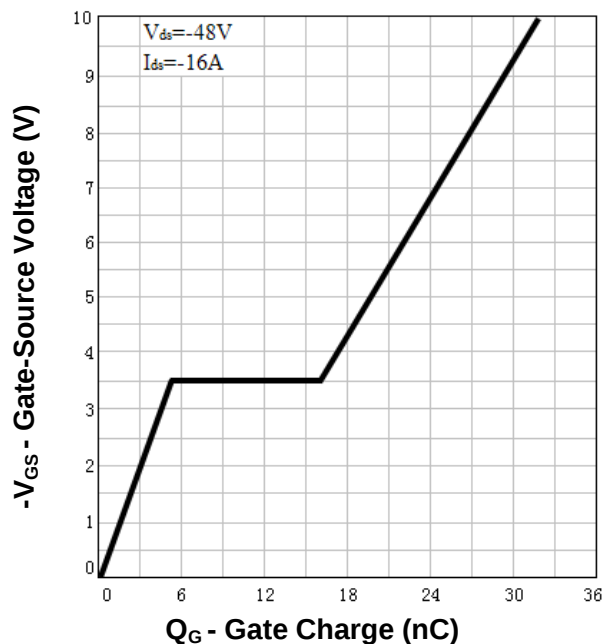
$-V_{SD}$ - Source-Drain Voltage (V)

Capacitance



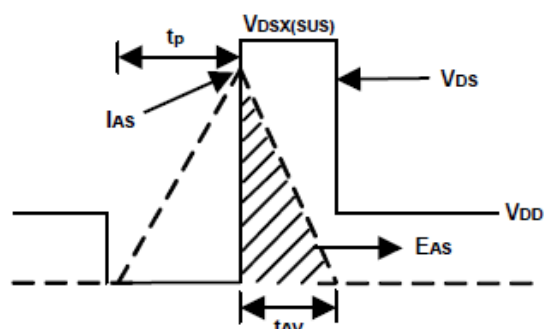
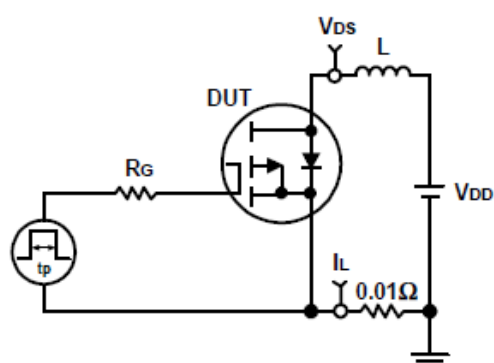
$-V_{DS}$ - Drain-Source Voltage (V)

Gate Charge

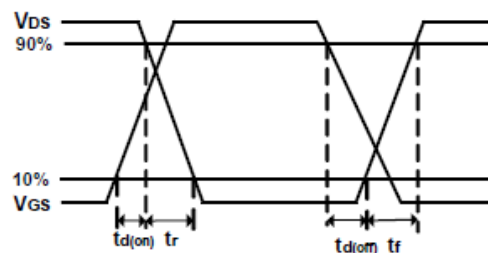
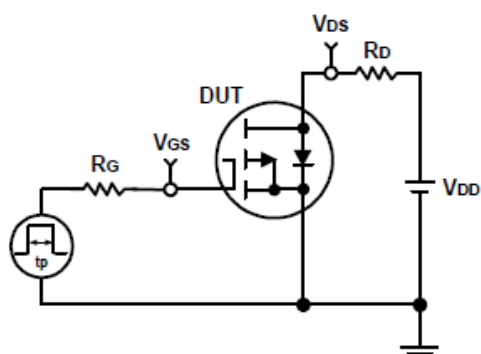


Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

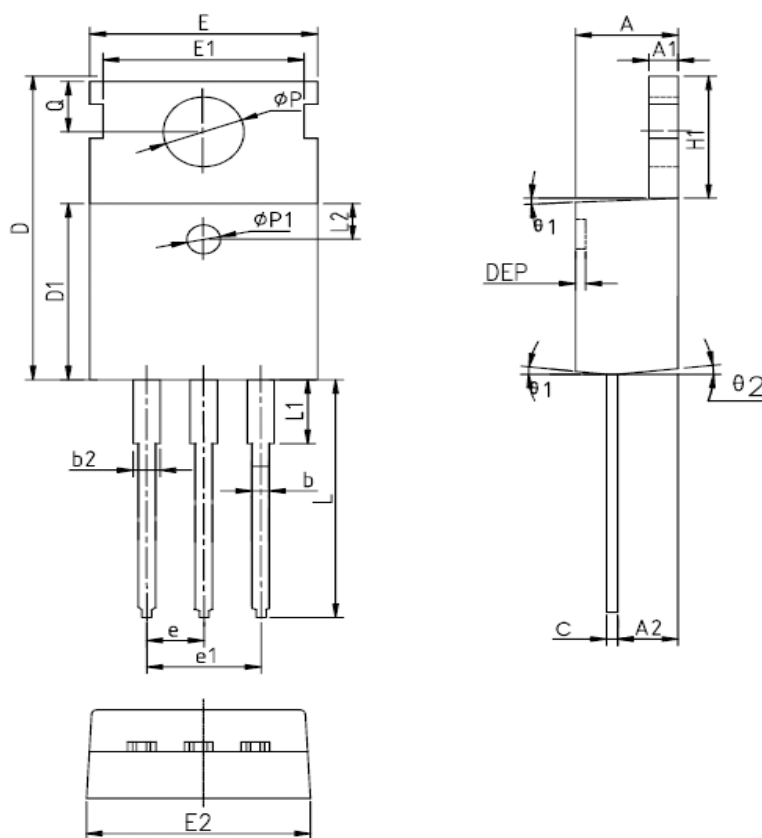


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU55L18R	RU55L18R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	Øp1	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	Øp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	θ 1	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	θ 2	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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